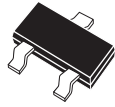


CBAS17

SURFACE MOUNT
LOW VOLTAGE
SILICON STABISTOR



SOT-23 CASE

CentralTM
Semiconductor Corp.

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CBAS17 type is a planar epitaxial silicon switching diode, designed for low voltage stabilizing applications.

MARKING CODE: A91

MAXIMUM RATINGS: ($T_A=25^\circ\text{C}$ unless otherwise noted)

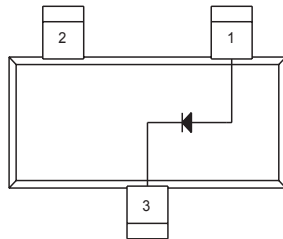
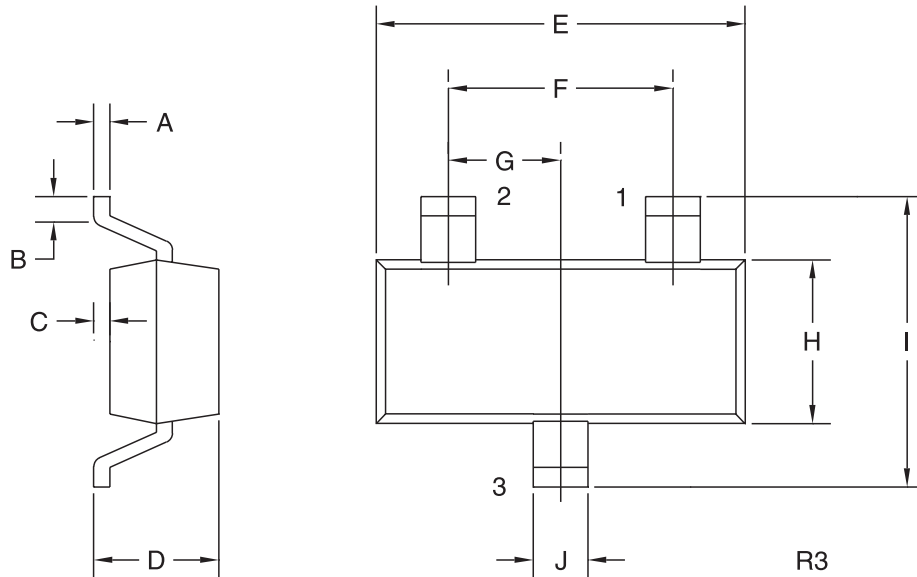
	SYMBOL		UNITS
Peak Repetitive Forward Current	I_{FRM}	250	mA
Power Dissipation	P_D	350	mW
Operating and Storage			
Junction Temperature	T_J, T_{stg}	-65 to +150	$^\circ\text{C}$
Thermal Resistance	Θ_{JA}	357	$^\circ\text{C/W}$

ELECTRICAL CHARACTERISTICS: ($T_A=25^\circ\text{C}$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
V_F	$I_F=0.1\text{mA}$.580	.665	.680	V
V_F	$I_F=1.0\text{mA}$.665	.745	.760	V
V_F	$I_F=5.0\text{mA}$.725	.805	.820	V
V_F	$I_F=10\text{mA}$.750	.825	.840	V
V_F	$I_F=100\text{mA}$.870	.920	.960	V
I_R	$V_R=4.0\text{V}$			5.0	μA
C_T	$V_R=0, f=1\text{MHz}$			140	pF

R5 (6- August 2003)

SOT-23 CASE - MECHANICAL OUTLINE



LEAD CODE:

- 1) ANODE
- 2) NO CONNECTION
- 3) CATHODE

MARKING CODE: A91

SYMBOL	DIMENSIONS			
	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.003	0.007	0.08	0.18
B	0.006	-	0.15	-
C	-	0.005	-	0.13
D	0.035	0.043	0.89	1.09
E	0.110	0.120	2.80	3.05
F	0.075		1.90	
G	0.037		0.95	
H	0.047	0.055	1.19	1.40
I	0.083	0.098	2.10	2.49
J	0.014	0.020	0.35	0.50

SOT-23 (REV: R3)